



20V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
20V	0.99Ω @ V _{GS} = 4.5V	0.54A
	1.2Ω @ V _G S = 2.5V	0.49A
	1.8Ω @ V _{GS} = 1.8V	0.4A
	2.4Ω @ V _{GS} = 1.5V	0.35A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

Features and Benefits

- Low Package Profile
- 0.6mm x 0.4mm Package Footprint
- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.0V Max
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
 - For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

 https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: X2-DFN0604-3
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (e4)
- Weight: 0.001 grams (Approximate)

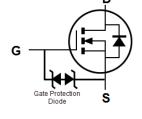
X2-DFN0604-3











Top View Package Pin Configuration

Equivalent Circuit

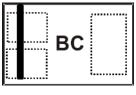
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2991UFO-7B	X2-DFN0604-3	10k/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



BC= Product Type Marking Code Bar Denotes Gate and Source Side

Top View



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			Vgss	±8	V
Continuous Drain Current (Note 5) V 4 5V	Steady T _A = +25°C		l _n	0.54	Δ.
Continuous Drain Current (Note 5) V _{GS} = 4.5V	State	T _A = +85°C	ID	0.43] ^
Pulsed Drain Current (Note 6)			I _{DM}	1.2	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	Steady State	P _D	0.44	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	281	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

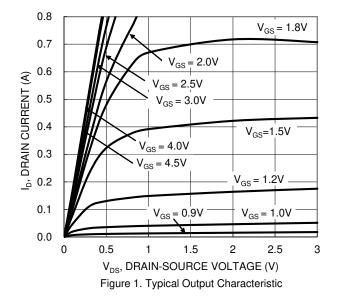
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

0			-			T 10 150	
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)				•			
Drain-Source Breakdown Voltage	BVDSS	20	_	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	-	_	1	μΑ	$V_{DS} = 16V$, $V_{GS} = 0V$	
Gate-Source Leakage	Igss		_	±10	μA	$V_{GS} = \pm 5V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	0.4	_	1.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
		_	0.5	0.99		V _{GS} = 4.5V, I _D = 100mA	
Static Drain-Source On-Resistance	Dagger	_	0.6	1.2		$V_{GS} = 2.5V, I_{D} = 50mA$	
Static Drain-Source On-Resistance	RDS(ON)	_	0.8	1.8	Ω	V _{GS} = 1.8V, I _D = 20mA	
		_	1.0	2.4		V _{GS} = 1.5V, I _D = 10mA	
Diode Forward Voltage	V _{SD}	_	0.7	1.0	V	V _{GS} = 0V, I _S = 150mA	
DYNAMIC CHARACTERISTICS (Note 8)	•		•	•	•	•	
Input Capacitance	Ciss	_	21.5	_	pF	T.,	
Output Capacitance	Coss	_	4.9	_	pF	V _{DS} = 15V, V _{GS} = 0V, -f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	3.7	_	pF	1 - 1.000112	
Gate Resistance	Rg	_	0.94	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1.0MHz$	
Total Gate Charge	Qg	_	0.35	_	nC	V 45V V 40V	
Gate-Source Charge	Qgs	_	0.07	_	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 250mA	
Gate-Drain Charge	Qgd	_	0.08	_	nC		
Turn-On Delay Time	td(ON)	_	5.6	_	ns	$\begin{aligned} & V_{DD} = 10V, \ V_{GS} = 4.5V, \\ & R_L = 47\Omega, \ R_g = 10\Omega, \\ & I_D = 200 mA \end{aligned}$	
Turn-On Rise Time	t _R	_	4.9	_	ns		
Turn-Off Delay Time	tD(OFF)	_	60.6	_	ns		
Turn-Off Fall Time	tF	_	27.6	_	ns		

Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
 6. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to product testing.





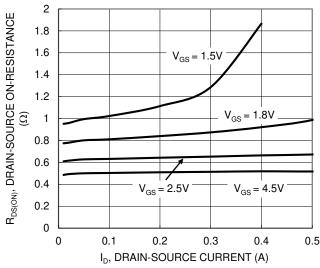


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

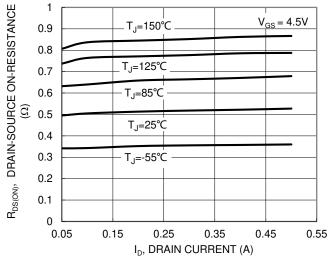


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

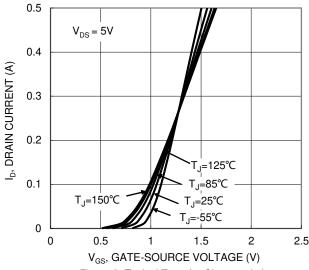


Figure 2. Typical Transfer Characteristic

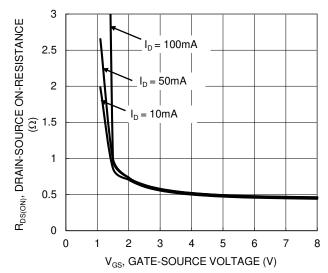


Figure 4. Typical Transfer Characteristic

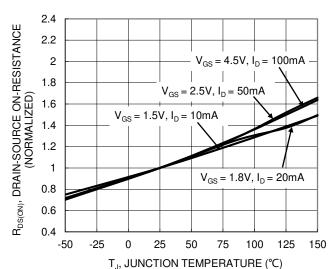


Figure 6. On-Resistance Variation with Junction Temperature



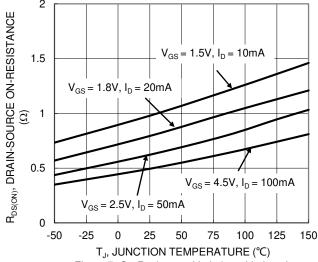
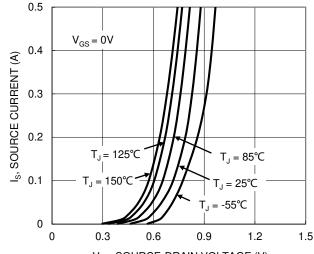


Figure 7. On-Resistance Variation with Junction Temperature



V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current

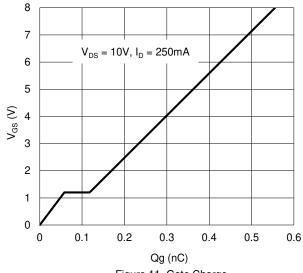


Figure 11. Gate Charge

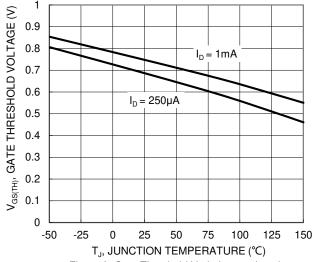
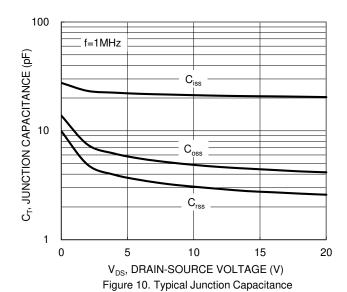


Figure 8. Gate Threshold Variation vs. Junction Temperature





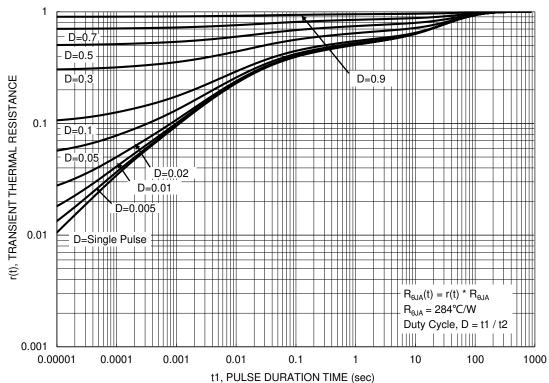


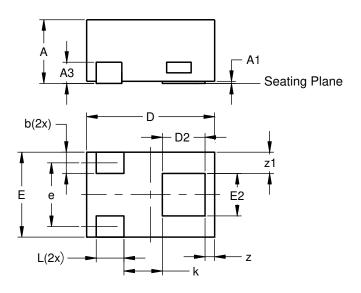
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

 $Please \ see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$

X2-DFN0604-3

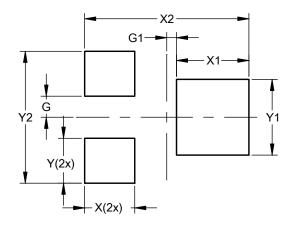


X2-DFN0604-3					
Dim	Min	Max	Тур		
Α		0.40	0.36		
A1	0.00	0.03	0.02		
A3			0.10		
b	0.07	0.15	0.10		
D	0.55	0.65	0.60		
D2	0.15	0.25	0.20		
E	0.35	0.45	0.40		
E2	0.15	0.25	0.20		
e	-	-	0.30		
k	0.15	-			
L	0.10	0.18	0.13		
Z			0.045		
z1			0.10		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN0604-3



Dimensions	Value (in mm)			
G	0.075			
G1	0.035			
X	0.180			
X1	0.260			
X2	0.590			
Y	0.160			
Y1	0.270			
Y2	0.470			



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